

REMARKS

The present application includes claims 1-24. By this Preliminary Amendment, claims 1-24 have been canceled and new claims 25-33 have been added.

The present application is a continuation of Application No. 09/658,222 filed September 8, 2000, which issued as U.S. Patent No. 6,653,707.

New claims 25-33 include independent claims 25 and 31. Independent claim 25 recites a method for creating a semiconductor device, including forming a base layer on a semiconductor layer, forming a dielectric layer on the base layer, establishing an opening in the base layer and an opening in the dielectric layer, then positioning a conductive contact within the opening in the base layer and the opening in the dielectric layer, where the lateral extent of the opening in the base layer is larger than the lateral extent of the opening in the dielectric layer.

Independent claim 31 is similar to independent claim 25, but recites the limitation that the conductive contact does not contact the first layer.

The applicant respectfully requests entry and examination of the above claims.

Application No. 10/684,910
Attorney Docket No. 12734US02


CONCLUSION

If the Examiner has any questions or the Applicant can be of any assistance, the Examiner is invited and encouraged to contact the Applicant at the number below.

The Commissioner is authorized to charge any necessary fees or credit any overpayment to the Deposit Account of McAndrews, Held & Malloy, Account No. 13-0017.

Respectfully submitted,

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